



3.3 Volt Synchronous x18 First-In/First-Out Queue

Memory Configuration	Device
4,096 x 18	FQV245
2,048 x 18	FQV235
1,024 x 18	FQV225
512 x 18	FQV215
256 x 18	FQV205

Key Features:

- Industry leading First-In/First-Out Queues (up to 133MHz)
- Independent Write and Read cycle time
- 3.3V power supply
- 5V input tolerant on all control and data input pins
- 5V output tolerant on all flags and data output pins
- Reset clears all previously programmed configurations including Write and Read pointers.
- Preset for Almost Full (PRAF) and Almost Empty (PRAE) offsets values
- Parallel programming of PRAF and PRAE offset values
- Full, Empty, Almost Full, Almost Empty, and Half Full indicators
- Asynchronous output enable tri-state data output drivers
- Available package: 64 - pin Plastic Thin Quad Flat Package (TQFP), 64 - pin Slim Thin Quad Flat Package (STQFP)
- (0°C to 70°C) Commercial operating temperature available for cycle time of 7.5ns and above
- (-40°C to 85°C) Industrial operating temperature available for cycle time of 10ns and above

Product Description:

HBA's FlexQ™ I offers industry leading FIFO queuing bandwidth (up to 2.4 Gbps), with a wide range of memory configurations (from 256 x 18 to 4,096 x 18). System designer has full flexibility of implementing deeper and wider queues with Write (WEXI and WEXO) and Read (REXI and REXO) expansion features using daisy chain technique. Full, Empty, and Half Full indicators allow easy handshaking between transmitters and receivers. User programmable Almost Full and Almost Empty (Parallel) indicators allow implementation of virtual queue depths.

5V tolerant on all input and output pins allow easy interfacing with devices operating at higher voltage levels. Asynchronous Output Enable pin configures the tri-state data output drivers. Independent Write and Read controls provide rate-matching capability.

Data is written into the queue at the low to high transition of WCLK if WEN is asserted. Data is read from the queue at the low to high transition of RCLK if REN is asserted.

Reset clears all previously programmed configurations by providing a low pulse on RST pin. In addition, Write and Read pointers to the queue are initialized to zero.

These FlexQ™ I devices have low power consumption, hence minimizing system power requirements. In addition, industry standard 64 - pin Plastic TQFP and 64 - pin STQFP are offered to save system board space.

These queues are ideal for applications such as data communication, telecommunication, graphics, multiprocessing, test equipment, network switching, etc.

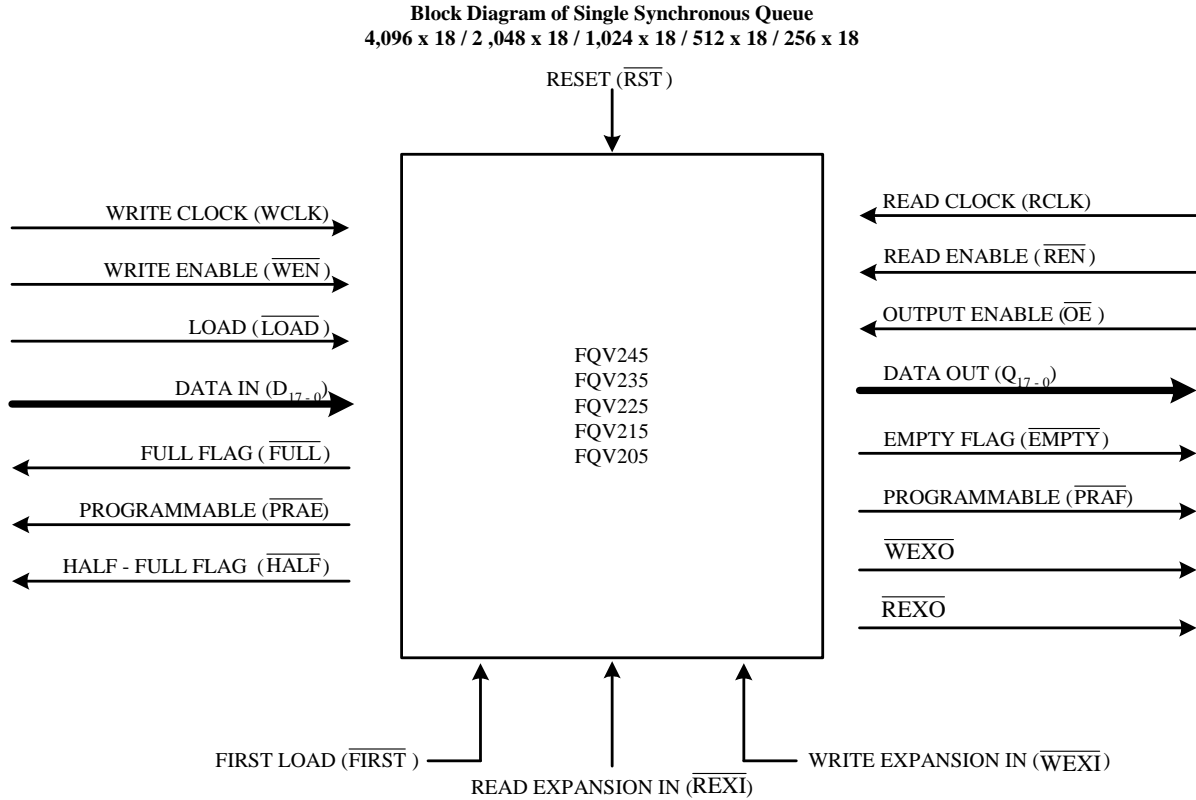


Figure 1. Single Device Configuration Signal Flow Diagram

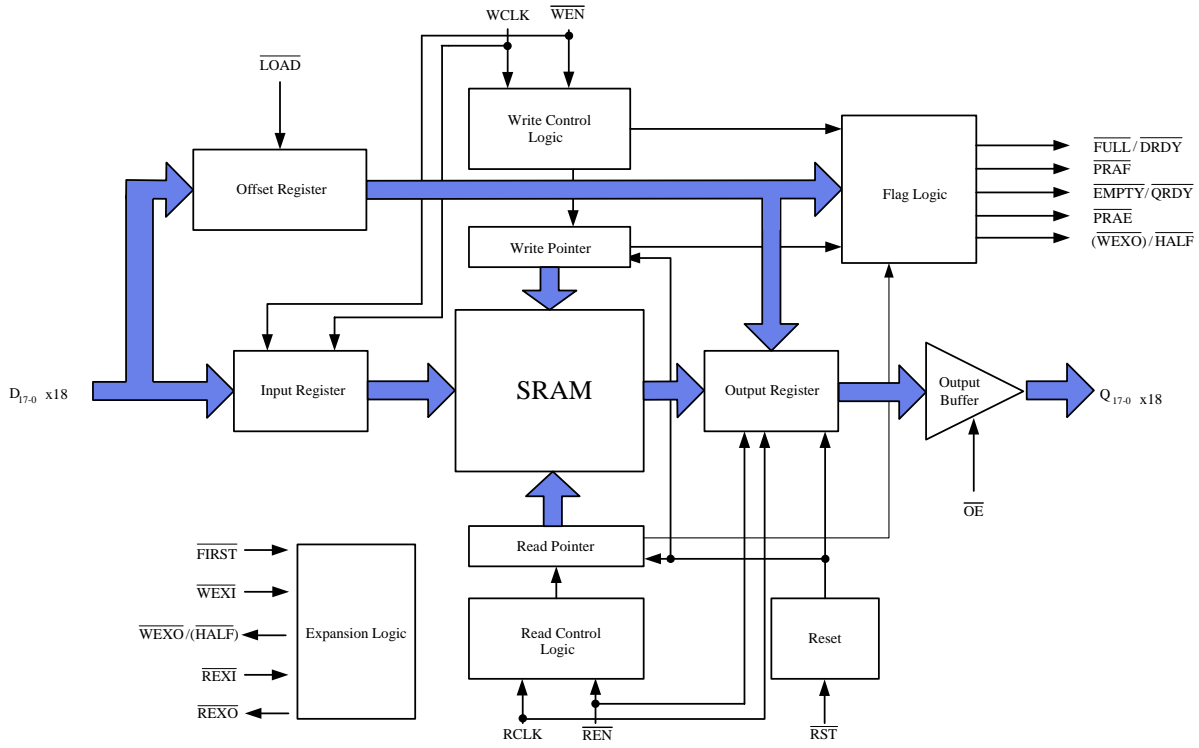
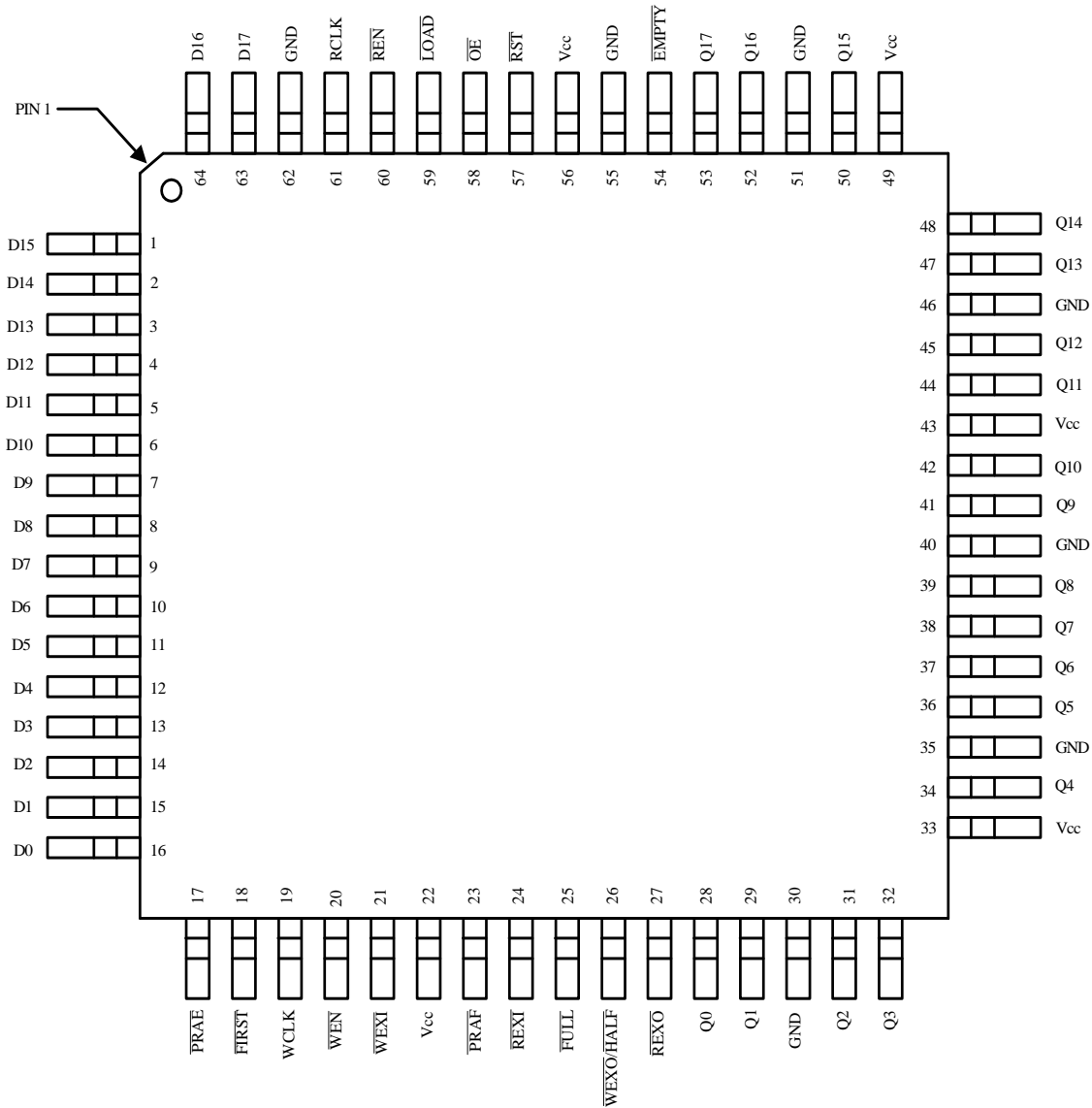


Figure 2. Device Architecture



TQFP – 64 (Drw No: PF-01A; Order Code: PF)
 STQFP – 64 (Drw No: TF-01A; Order Code: TF)
 Top View

Figure 3. Device Pin Out



Pin #	Pin Name	Pin Symbol	Input/Output	Description
57	Reset	\overline{RST}	Input	Reset is required to initialize Write and Read pointers to the first position of the queue by setting \overline{RST} low. \overline{FULL} and \overline{PRAF} will go high; \overline{EMPTY} and \overline{PRAE} will go low. All data outputs will go low. Previous programmed configurations will not be maintained.
19	Write Clock	WCLK	Input	Writes data into queue during low to high transitions of WCLK if \overline{WEN} is set low.
20	Write Enable	\overline{WEN}	Input	Controls write operation into queue or offset registers during low to high transition of WCLK.
59	Load Enable	\overline{LOAD}	Input	\overline{LOAD} controls write/read, to/from offset registers during low to high transition of WCLK/RCLK respectively. Use in conjunction with \overline{WEN} / \overline{REN} .
18	First Load	\overline{FIRST}	Input	In single device configuration, \overline{FIRST} is set low. In depth expansion configuration, \overline{FIRST} is set low for the first device and set high for other devices in the daisy chain.
21	Write Expansion In	\overline{WEXI}	Input	In single device configuration, \overline{WEXI} is set low. In depth expansion configuration, \overline{WEXI} is connected to \overline{WEXO} of previous device in the daisy chain.
63, 64, 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11, 12, 13, 14, 15, 16	Data Inputs	D ₁₇₋₀	Input	18 - bit wide input data bus.
61	Read Clock	RCLK	Input	Reads data from queue during low to high transitions of RCLK if \overline{REN} is set low.
60	Read Enable	\overline{REN}	Input	Controls read operation from queue or offset registers during low to high transition of RCLK.
24	Read Expansion In	\overline{REXI}	Input	In single device configuration, \overline{REXI} is set low. In depth expansion configuration, \overline{REXI} is connected to \overline{REXO} of previous device in the daisy chain.
58	Output Enable	\overline{OE}	Input	Setting \overline{OE} low activates the data output drivers. Setting \overline{OE} high deactivates the data output drivers (High-Z).
53, 52, 50, 48, 47, 45, 44, 42, 41, 39, 38, 37, 36, 34, 32, 31, 29, 28	Data Outputs	Q ₁₇₋₀	Output	18 - bit wide output data bus.
27	Read Expansion Out	\overline{REXO}	Output	In depth expansion configuration, \overline{REXO} is connected to \overline{REXI} of next device in the daisy chain.
25	Full Flag	\overline{FULL}	Output	Queue is full when \overline{FULL} goes low during the low to high transition of WCLK. This prohibits further writes into the queue.

Table 1. Pin Descriptions

Pin #	Pin Name	Pin Symbol	Input/Output	Description
54	Empty Flag	$\overline{\text{EMPTY}}$	Output	Queue is empty when $\overline{\text{EMPTY}}$ goes low during the low to high transition of RCLK. This prohibits further reads from the queue.
23	Almost Full	$\overline{\text{PRAF}}$	Output	Queue is almost full when $\overline{\text{PRAF}}$ goes low during the low to high transition of WCLK. Default (Full-offset) or programmed offset values determine the status of $\overline{\text{PRAF}}$.
17	Almost Empty	$\overline{\text{PRAE}}$	Output	Queue is almost empty when $\overline{\text{PRAE}}$ goes low during the low to high transition of RCLK. Default (Empty+offset) or programmed offset values determine the status of $\overline{\text{PRAE}}$.
26	Write Expansion Out/Half Full	$\overline{\text{WEXO}} / \overline{\text{HALF}}$	Output	In single device configuration, queue is more than half full when $\overline{\text{WEXO}} / \overline{\text{HALF}}$ goes low. In depth expansion configuration, $\overline{\text{WEXO}} / \overline{\text{HALF}}$ is connected to $\overline{\text{WEXI}}$ of next device in the daisy chain.
22, 33, 43, 49, 56	Power	Vcc	N/A	3.3V power supply.
30, 35, 40, 46, 51, 55, 62	Ground	GND	N/A	0V Ground.

Table 1. Pin Descriptions (Continued)



Make Memory Smarter™

Symbol	Rating	Com'l & Ind'l	Unit
V _{TERM}	Terminal Voltage with respect to GND	-0.5 to +5.0	V
T _{STG}	Storage Temperature	-55 to +125	°C
I _{OUT}	DC Output Current	-50 to +50	mA

NOTES:

Absolute Max Ratings are for reference only. Permanent damage to the device may occur if extended period of operation is outside this range. Standard operation should fall within the Recommended Operating Conditions.

Table 2. Absolute Maximum Ratings

		FQV245 FQV235 FQV225 FQV215 FQV205						
		Commercial Clock = 7.5ns, 10ns, 15ns, 20ns			Industrial Clock = 10ns, 15ns, 20ns			
Symbol	Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Unit
Recommended Operating Conditions								
V _{CC}	Supply Voltage Com'l/Ind'l	3.0	3.3	3.6	3.0	3.3	3.6	V
GND	Supply Voltage	0	0	0	0	0	0	V
V _{IH}	Input High Voltage Com'l/Ind'l	2.0	-	5.5	2.0	-	5.5	V
V _{IL}	Input Low Voltage Com'l/Ind'l	-	-	0.8	-	-	0.8	V
T _A	Operating Temperature Commercial	0	-	70	0	-	70	°C
T _A	Operating Temperature Industrial	-40	-	85	-40	-	85	°C
DC Electrical Characteristics								
I _{LI} ⁽¹⁾	Input Leakage Current (any input)	-10	-	10	-10	-	10	μA
I _{LO}	Output Leakage Current	-10	-	10	-10	-	10	μA
V _{OH}	Output Logic "1" Voltage, IOH=-2mA	2.4	-	-	2.4	-	-	V
V _{OL}	Output Logic "0" Voltage, IOL = 8mA	-	-	0.4	-	-	0.4	V
Power Consumption								
I _{CC1} ^(2,3)	Active Power Supply Current	-	-	30	-	-	30	mA
I _{CC2} ⁽⁴⁾	Standby Current	-	-	5	-	-	5	mA

Table 3. DC Specifications



Make Memory Smarter™

Capacitance at 1.0 MHz Ambient Temperature (25°C)				
Symbol	Parameter	Conditions	Max.	Unit
$C_{IN}^{(2)}$	Input Capacitance	$V_{IN} = 0V$	10	pF
$C_{OUT}^{(2,4)}$	Output Capacitance	$V_{OUT} = 0V$	10	pF

NOTES:

1. Measurement with $0.4 \leq V_{IN} \leq V_{CC}$
2. With output tri-stated ($\overline{OE} = \text{High}$)
3. $I_{CC(1,2)}$ is measured with WCLK and RCLK at 20 MHz
4. Design simulated, not tested.

Table 3. DC Specifications (Continued)



Make Memory Smarter™

Symbol	Parameter	Commercial		Commercial & Industrial						Unit		
		Min.	Max.	FQV245-7.5 FQV235-7.5 FQV225-7.5 FQV215-7.5 FQV205-7.5		FQV245-10 FQV235-10 FQV225-10 FQV215-10 FQV205-10		FQV245-15 FQV235-15 FQV225-15 FQV215-15 FQV205-15			FQV245-20 FQV235-20 FQV225-20 FQV215-20 FQV205-20	
				Min.	Max.	Min.	Max.	Min.	Max.		Min.	Max.
fs	Clock Cycle Frequency	-	133	-	100	-	66	-	50	MHz		
tA	Data Access Time	1	5	2	6.5	2	10	2	12	ns		
tWCLK	Write Clock Cycle Time	7.5	-	10	-	15	-	20	-	ns		
tWCLKH	Write Clock High Time	3.5	-	4.5	-	6	-	8	-	ns		
tWCLKL	Write Clock Low Time	3.5	-	4.5	-	6	-	8	-	ns		
tRCLK	Read Clock Cycle Time	7.5	-	10	-	15	-	20	-	ns		
tRCLKH	Read Clock High Time	3.5	-	4.5	-	6	-	8	-	ns		
tRCLKL	Read Clock Low Time	3.5	-	4.5	-	6	-	8	-	ns		
tDS	Data Set-up Time	2.5	-	3	-	4	-	5	-	ns		
tDH	Data Hold Time	0.5	-	0.5	-	1	0	1	-	ns		
tENS	Enable Set-up Time	2.5	-	3	-	4	-	5	-	ns		
tENH	Enable Hold Time	0.5	-	0.5	-	1	-	1	-	ns		
tRST	Reset Pulse Width ⁽¹⁾	10	-	10	-	15	-	20	-	ns		
tRSTS	Reset Set-up Time	8	-	8	-	10	-	12	-	ns		
tRSTR	Reset Recovery Time	8	-	8	-	10	-	12	-	ns		
tRSTF	Reset to Flag and Output Time	-	12	-	15	-	15	-	20	ns		
tOLZ	Output Enable to Output in Low-Z ⁽²⁾	0	-	0	-	0	-	0	-	ns		
tOE	Output Enable to Output Valid	2	5	3	6	3	8	3	10	ns		
tOHZ	Output Enable to Output in High-Z ⁽²⁾	2	5	3	6	3	8	3	10	ns		
tFULL	Write Clock to Full Flag	-	5	-	6.5	-	10	-	12	ns		
tEMPTY	Read Clock to Empty Flag	-	5	-	6.5	-	10	-	12	ns		
tPRAF	Clock to Programmable Almost-Full Flag	-	13	-	17	-	20	-	22	ns		
tPRAE	Clock to Programmable Almost-Empty Flag	-	13	-	17	-	20	-	22	ns		
tHALF	Clock to Half-Full Flag	-	13	-	17	-	20	-	22	ns		
tXO	Clock to Expansion Out	-	5	-	6.5	-	10	-	12	ns		
tXI	Expansion in Pulse Width	3	-	3	-	6.5	-	8	-	ns		
tXIS	Expansion in Set-Up Time	3.5	-	5	-	5	-	8	-	ns		
tSKEW1	Skew time between Read Clock & Write Clock for Full Flag	4	-	5	-	6	-	8	-	ns		
tSKEW2	Skew time between Read Clock & Write Clock for Empty Flag	4	-	5	-	6	-	8	-	ns		

NOTES:

1. Pulse widths less than minimum values are not allowed.
2. Design simulated, not tested.

Table 4. AC Electrical Characteristics

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns ⁽¹⁾
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load*, clock = 10ns, 15ns, 20ns	See Figure 5
Output Load, clock = 7.5ns	See Figure 4

*Include jig and scope capacitances

Notes:

1. For 133MHz, operation input rise/fall times are 1.5ns.

Table 5. AC Test Condition

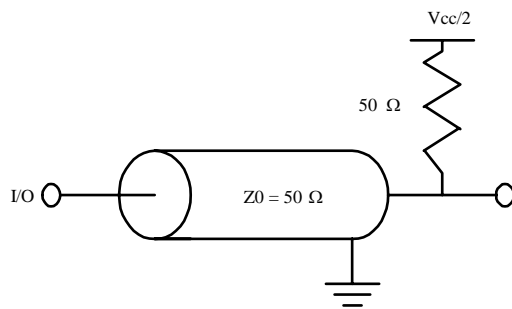


Figure 4. AC Test Load
for clock = 7.5ns

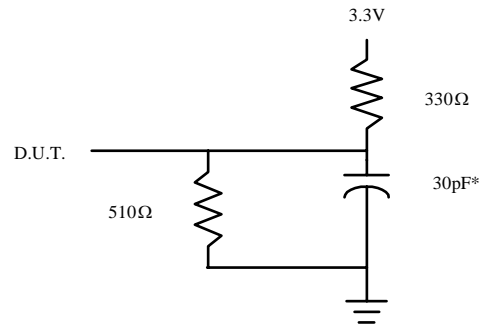


Figure 5. Output Load
for clock = 10ns, 15ns, 20ns
*Includes jig and scope capacitances.

Pin Functions

$\overline{\text{RST}}$	Reset is required to initialize Write and Read pointers to the first position of the queue by setting $\overline{\text{RST}}$ low. $\overline{\text{FULL}}$ and $\overline{\text{PRAF}}$ will go high; $\overline{\text{EMPTY}}$ and $\overline{\text{PRAE}}$ will go low. All data outputs will go low. Previous programmed configurations will not be maintained.
WCLK	Writes data into queue during low to high transitions of WCLK if $\overline{\text{WEN}}$ is set low. Synchronizes $\overline{\text{FULL}}$ and $\overline{\text{PRAF}}$ flags. WCLK and RCLK are independent of each other.
$\overline{\text{WEN}}$	Controls write operation into queue or offset registers during low to high transition of WCLK.
$\overline{\text{LOAD}}$	$\overline{\text{LOAD}}$ controls write/read, to/from offset registers during low to high transition of WCLK/RCLK respectively for parallel programming. Use in conjunction with $\overline{\text{WEN}} / \overline{\text{REN}}$.
$\overline{\text{FIRST}}$	In single device configuration, $\overline{\text{FIRST}}$ is set low. In depth expansion configuration, $\overline{\text{FIRST}}$ is set low for the first device and set high for other devices in the daisy chain.
$\overline{\text{WEXI}}$	In single device configuration, $\overline{\text{WEXI}}$ is set low. In depth expansion configuration, $\overline{\text{WEXI}}$ is connected to $\overline{\text{WEXO}}$ of previous device in the daisy chain.
D_{17-0}	18 - bit wide input data bus.
RCLK	Reads data from queue during low to high transitions of RCLK if $\overline{\text{REN}}$ is set low. Synchronizes the $\overline{\text{EMPTY}}$ and $\overline{\text{PRAE}}$ flags. RCLK and WCLK are independent of each other.
$\overline{\text{REN}}$	Reads data from queue during low to high transitions of RCLK if $\overline{\text{REN}}$ is set to low. This also advances the Read pointer of the queue.
$\overline{\text{OE}}$	Setting $\overline{\text{OE}}$ low activates the data output drivers. Setting $\overline{\text{OE}}$ high deactivates the data output drivers (High-Z). $\overline{\text{OE}}$ does not control advancement of Read pointer.
Q_{17-0}	18 - bit wide output data bus.
$\overline{\text{REXO}}$	In depth expansion configuration, $\overline{\text{REXO}}$ is connected to $\overline{\text{REXI}}$ of next device in the daisy chain.
$\overline{\text{FULL}}$	Queue is full when $\overline{\text{FULL}}$ goes low during the low to high transition of WCLK. This prohibits further writes into the queue and prevents advancement of Write pointer. Refer to Table 8 for behavior of $\overline{\text{FULL}}$.
$\overline{\text{EMPTY}}$	Queue is empty when $\overline{\text{EMPTY}}$ goes low during the low to high transition of RCLK. This prohibits further reads from the queue and prevents advancement of Read pointer. Refer to Table 8 for behavior of $\overline{\text{EMPTY}}$.
$\overline{\text{PRAF}}$	Queue is almost full when $\overline{\text{PRAF}}$ goes low during the low to high transition of WCLK. $\overline{\text{PRAF}}$ goes high during the low to high transition of RCLK. Default (Full-offset) or programmed offset values determine the status of $\overline{\text{PRAF}}$. Refer to Table 8 for behavior of $\overline{\text{PRAF}}$.
$\overline{\text{PRAE}}$	Queue is almost empty when $\overline{\text{PRAE}}$ goes low during the low to high transition of RCLK. $\overline{\text{PRAE}}$ goes high during the low to high transition of WCLK. Default (Empty+offset) or programmed offset values determine the status of $\overline{\text{PRAE}}$. Refer to Table 8 for behavior of $\overline{\text{PRAE}}$.
$\overline{\text{WEXO}} / \overline{\text{HALF}}$	In single device configuration, queue is more than half full when $\overline{\text{HALF}}$ goes low during the low to high transition of WCLK. Queue is less than half full when $\overline{\text{HALF}}$ goes high during the low to high transition of RCLK. Refer to Table 8 for details. In depth expansion configuration, $\overline{\text{WEXO}}$ is connected to $\overline{\text{WEXI}}$ of next device in the daisy chain
$\overline{\text{REXI}}$	In single device configuration, $\overline{\text{REXI}}$ is set low. In depth expansion configuration, $\overline{\text{REXI}}$ is connected to $\overline{\text{REXO}}$ of previous device in the daisy chain.

$\overline{\text{LOAD}}$	$\overline{\text{WEN}}$	$\overline{\text{REN}}$	WCLK	RCLK	FQV245 FQV235 FQV225 FQV215 FQV205 Selection / Sequence
0	0	1		X	Parallel write to offset registers: Empty Offset Full Offset Parallel write to registers: 1. $\overline{\text{PRAE}}$ 2. $\overline{\text{PRAF}}$
0	1	0	X		Parallel read from offset registers: Empty Offset Full Offset Parallel read from registers: 1. $\overline{\text{PRAE}}$ 2. $\overline{\text{PRAF}}$
X	1	1	X	X	No Operation
1	0	X		X	Write Memory
1	X	0	X		Read Memory

Figure 6. Programmable Flag Offset Programming Sequence

Device	$\overline{\text{PRAF}}$ Programming (bits)	$\overline{\text{PRAE}}$ Programming (bits)
FQV245	D/Q ₁₁₋₀	D/Q ₁₁₋₀
FQV235	D/Q ₁₀₋₀	D/Q ₁₀₋₀
FQV225	D/Q ₉₋₀	D/Q ₉₋₀
FQV215	D/Q ₈₋₀	D/Q ₈₋₀
FQV205	D/Q ₇₋₀	D/Q ₇₋₀

Table 6. Parallel Offset Register Data Mapping Table

Device	Default
FQV245	007FH
FQV235	007FH
FQV225	007FH
FQV215	003FH
FQV205	001FH

Table 7. Default Values of Offset Registers



FQV245	FULL	PRAF	HALF	PRAE	EMPTY
0	H	H	H	L	L
1 to $y^{(1)}$	H	H	H	L	H
$(y+1)$ to 2,048	H	H	H	H	H
2,049 to $[4,096-(x+1)]$	H	H	L	H	H
$(4,096 - x^{(2)})$ to 4,095	H	L	L	H	H
4,096	L	L	L	H	H

FQV235	FULL	PRAF	HALF	PRAE	EMPTY
0	H	H	H	L	L
1 to $y^{(1)}$	H	H	H	L	H
$(y+1)$ to 1,024	H	H	H	H	H
1,025 to $[2,048-(x+1)]$	H	H	L	H	H
$(2,048 - x^{(2)})$ to 2,047	H	L	L	H	H
2,048	L	L	L	H	H

FQV225	FULL	PRAF	HALF	PRAE	EMPTY
0	H	H	H	L	L
1 to $y^{(1)}$	H	H	H	L	H
$(y+1)$ to 512	H	H	H	H	H
513 to $[1,024-(x+1)]$	H	H	L	H	H
$(1,024 - x^{(2)})$ to 1,023	H	L	L	H	H
1,024	L	L	L	H	H

FQV215	FULL	PRAF	HALF	PRAE	EMPTY
0	H	H	H	L	L
1 to $y^{(1)}$	H	H	H	L	H
$(y+1)$ to 256	H	H	H	H	H
257 to $[512-(x+1)]$	H	H	L	H	H
$(512 - x^{(2)})$ to 511	H	L	L	H	H
512	L	L	L	H	H

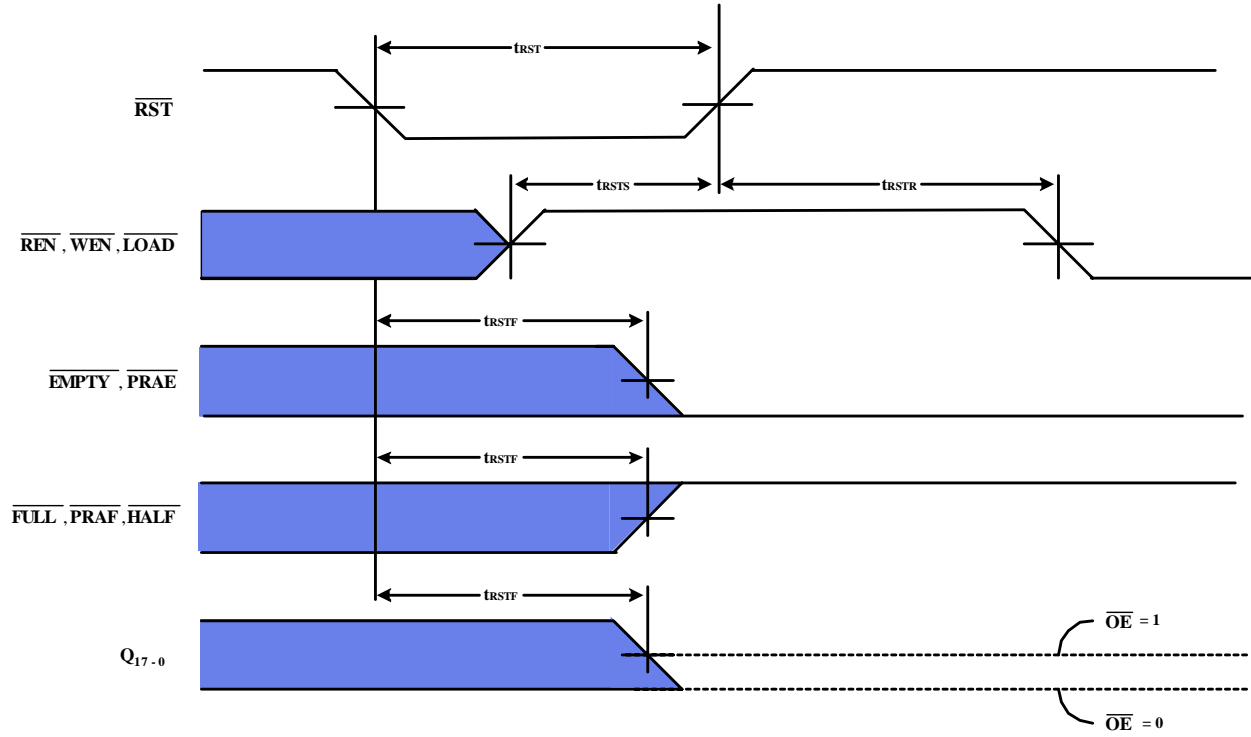
FQV205	FULL	PRAF	HALF	PRAE	EMPTY
0	H	H	H	L	L
1 to $y^{(1)}$	H	H	H	L	H
$(y+1)$ to 128	H	H	H	H	H
129 to $[256-(x+1)]$	H	H	L	H	H
$(256 - x^{(2)})$ to 255	H	L	L	H	H
256	L	L	L	H	H

NOTES:

- $y = \overline{\text{PRAE}}$ offset. Default Values: FQV205 $y = 31$, FQV215 $y = 63$, FQV245/FQV235/FQV225 $y = 127$.
- $x = \overline{\text{PRAF}}$ offset. Default Values: FQV205 $x = 31$, FQV215 $x = 63$, FQV245/FQV235/FQV225 $x = 127$.

Table 8. Status Flags

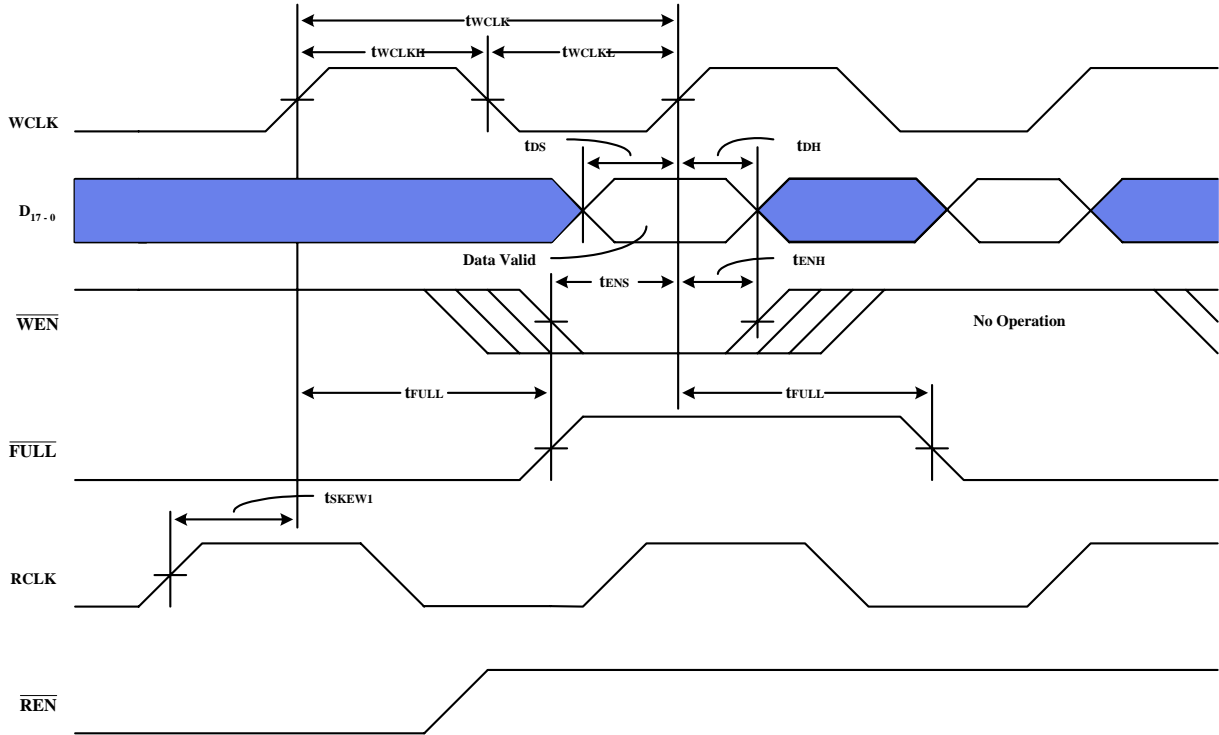
Timing Diagrams



NOTES:

1. After reset, the outputs will be low if $\overline{OE} = 0$ and tri-state if $\overline{OE} = 1$.
2. The clocks (RCLK, WCLK) can be free-running during reset.

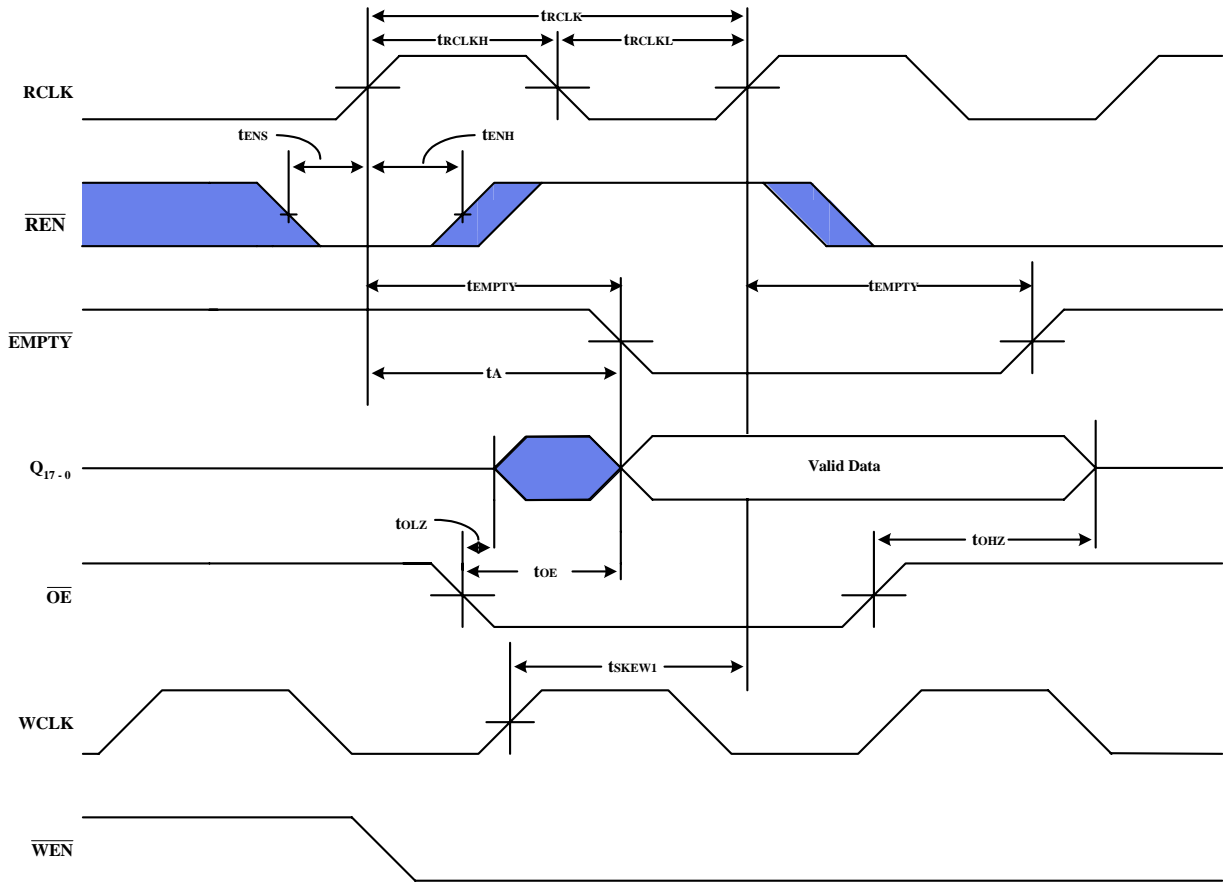
Diagram 1. Reset Timing



NOTES:

1. t_{SKEW1} is the minimum time between a rising RCLK edge and rising WCLK edge to guarantee that FULL will go high during the current clock cycle. If the time between the rising edge of RCLK and the rising edge of WCLK is equal to or less than t_{SKEW1}, then FULL may not change state until the next WCLK edge.

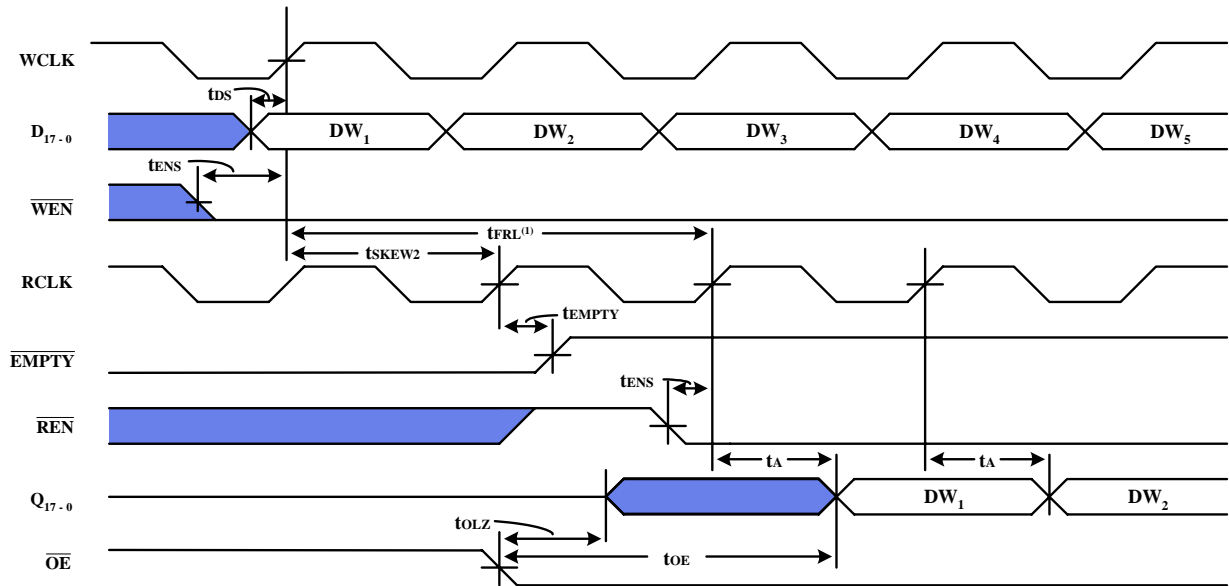
Diagram 2. Write Cycle Timing



NOTES:

1. t_{SKEW1} is the minimum time between a rising WCLK edge and a rising RCLK edge to guarantee that \overline{EMPTY} will go high during the current clock cycle. If the time between the rising edge of WCLK and the rising edge of RCLK is less than t_{SKEW1} , then \overline{EMPTY} may not change state until the next RCLK edge.

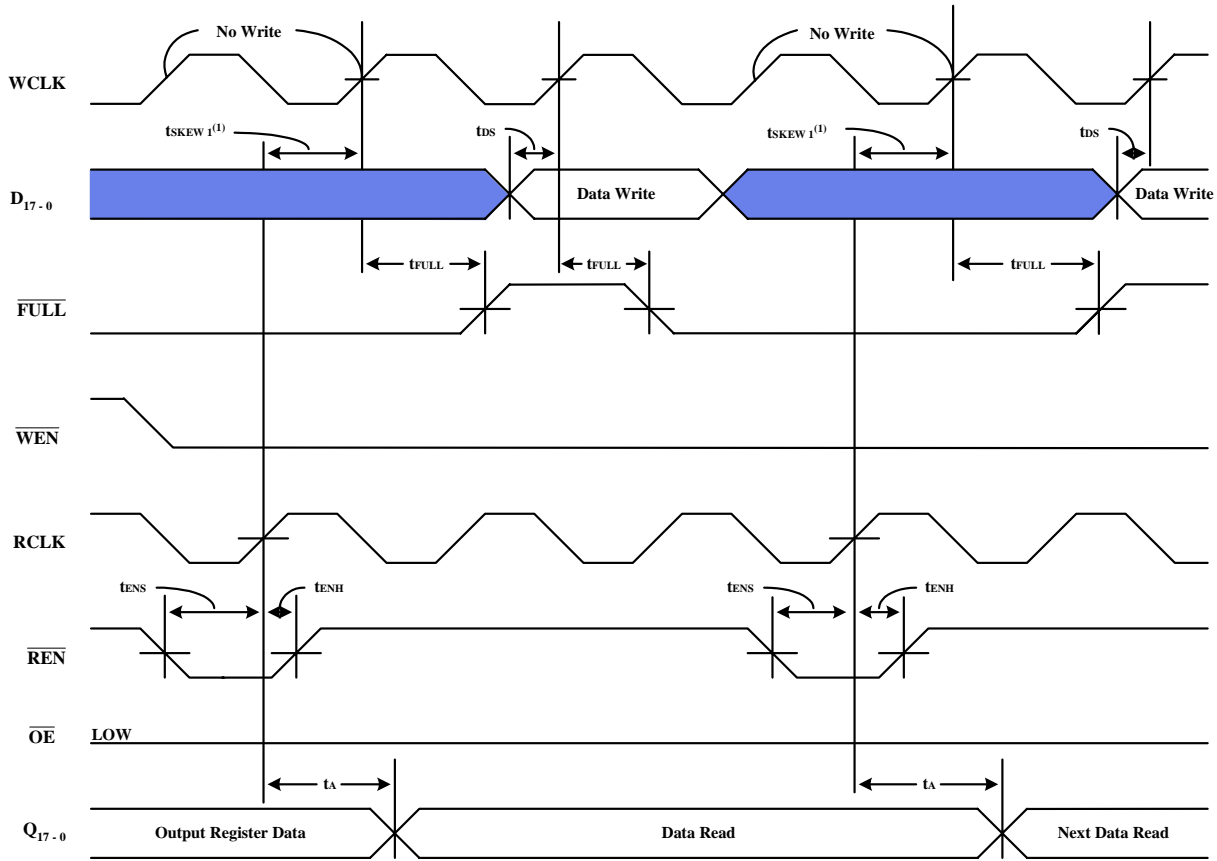
Diagram 3. Read Cycle Timing



NOTES:

- t_{FRL} is the latency from first write to first Read. When t_{SKEW2} is greater than or equal to minimum specification, t_{FRL} (maximum) = t_{RCLK} + t_{SKEW2}. When t_{SKEW2} is less than minimum specification, t_{FRL} (maximum) equals either 2* t_{RCLK} + t_{SKEW2} or t_{RCLK} + t_{SKEW2}. The Latency Timing applies only at the Empty Boundary (EMPTY = low).

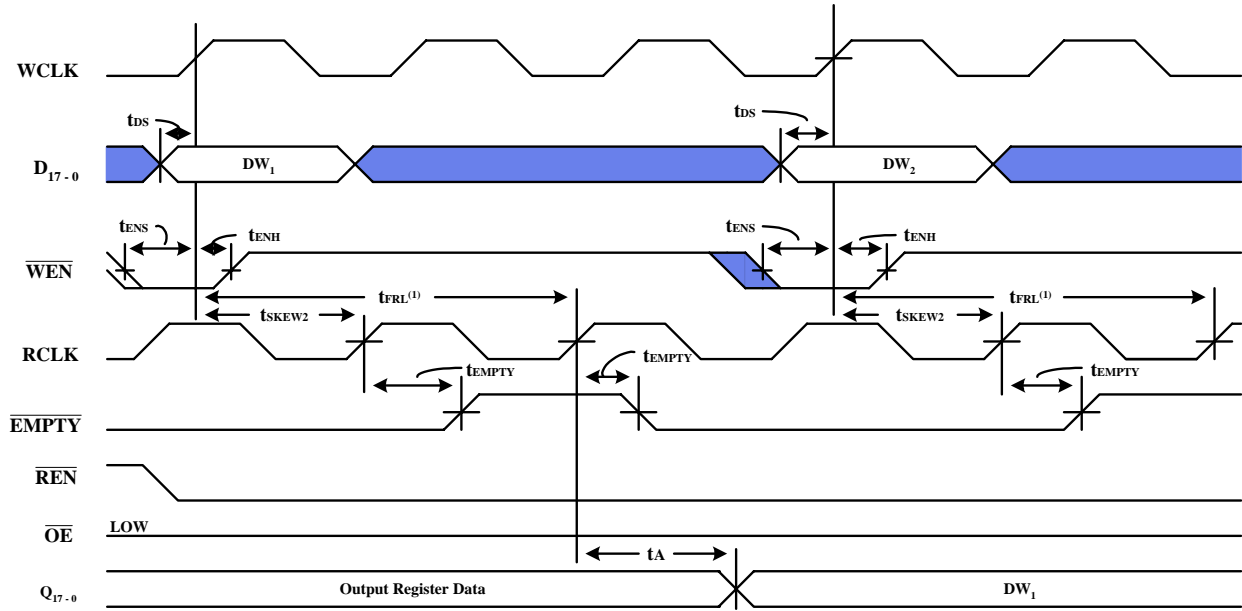
Diagram 4. First Data Word Latency after Reset with Simultaneous Read and Write



NOTES:

1. tsKEW1 is the minimum time between a rising RCLK edge and a rising WCLK edge to guarantee that FULL will go high during the current clock cycle. If the time between the rising edge of RCLK and the rising edge of WCLK is less than tsKEW1, then FULL may not change state until the next WCLK edge.

Diagram 5. Full Flag Timing



NOTES:

1. t_{FRL} is the latency from first write to first Read. When t_{SKEW2} is greater than or equal to minimum specification, t_{FRL} (maximum) = $t_{RCLK} + t_{SKEW2}$. When t_{SKEW2} less than minimum specification, t_{FRL} (maximum) equals either $2 * t_{RCLK} + t_{SKEW2}$, or $t_{RCLK} + t_{SKEW2}$. The Latency Timing applies only at the Empty Boundary (EMPTY = low).

Diagram 6. Empty Flag Timing

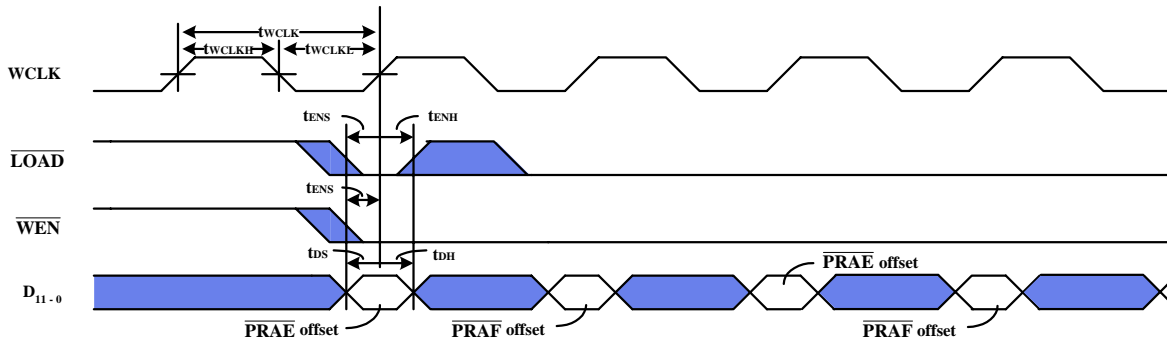


Diagram 7. Write Programmable Registers

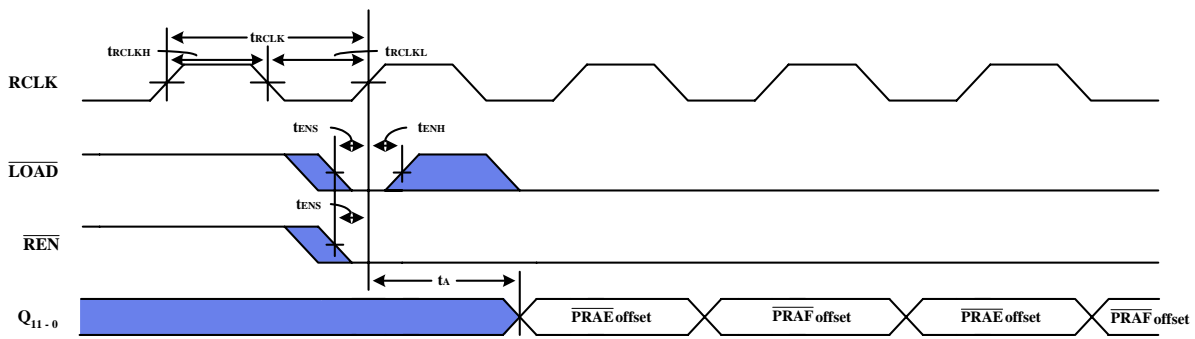
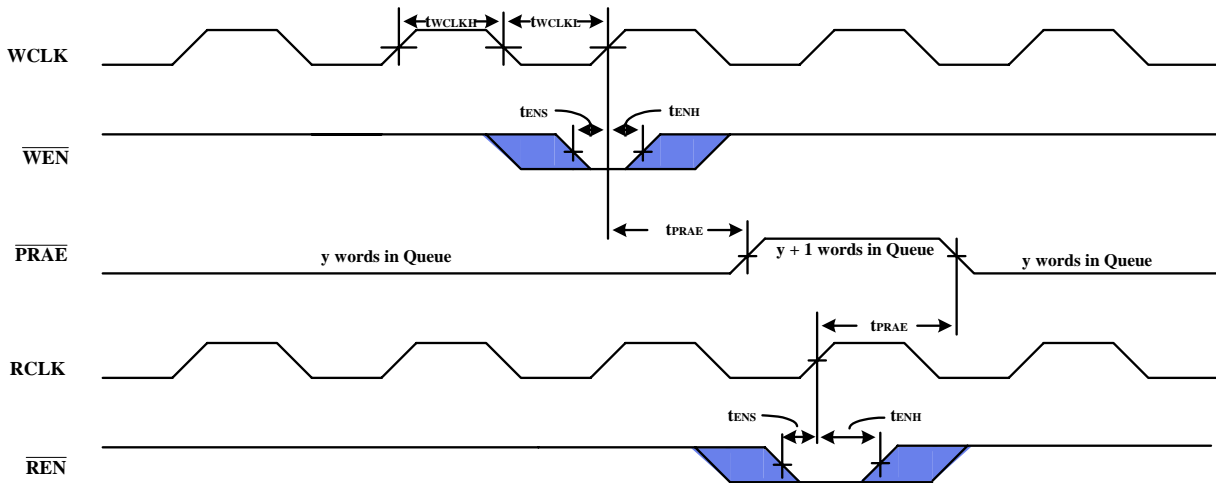


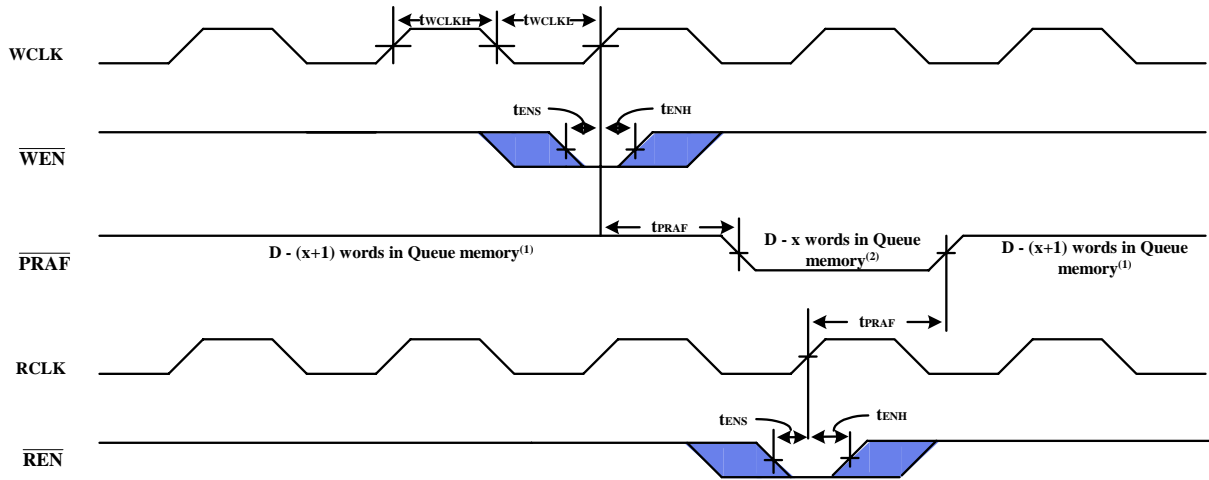
Diagram 8. Read Programmable Registers



NOTES:

1. $y = \overline{\text{PRAE}}$ offset.

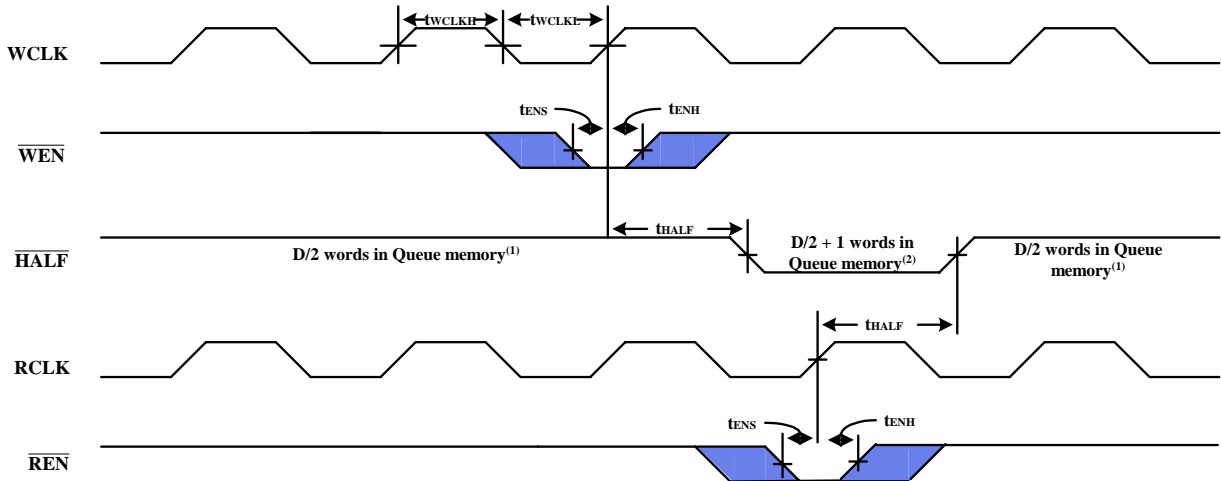
Diagram 9. Programmable Almost-Empty Flag Timing



NOTES:

1. $x = \text{PRAF offset}$.
2. $D = \text{maximum queue depth} = 256 \text{ words for FQV205; } 512 \text{ words for FQV215; } 1,024 \text{ words for FQV225; } 2,048 \text{ words for FQV235; and } 4,096 \text{ words for FQV245.}$

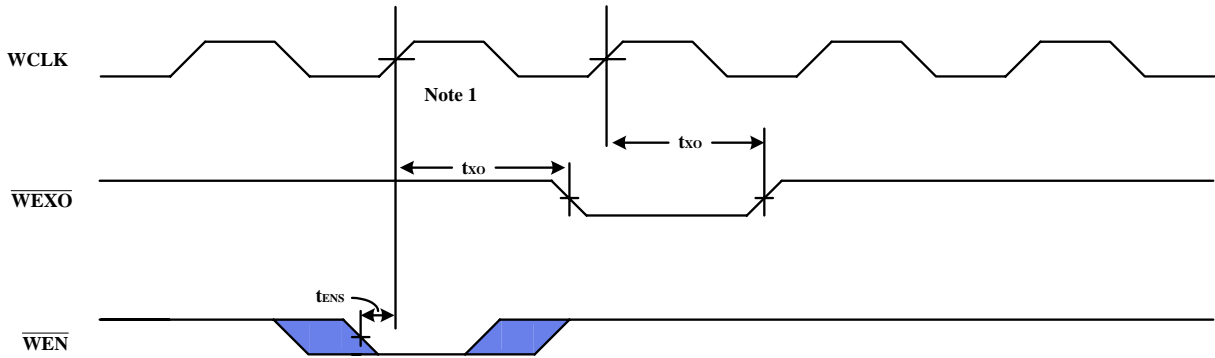
Diagram 10. Programmable Almost-Full Flag Timing



NOTES:

1. $D = \text{maximum queue depth} = 256 \text{ words for FQV205; } 512 \text{ words for FQV215; } 1,024 \text{ words for FQV225; } 2,048 \text{ words for FQV235; and } 4,096 \text{ words for FQV245.}$

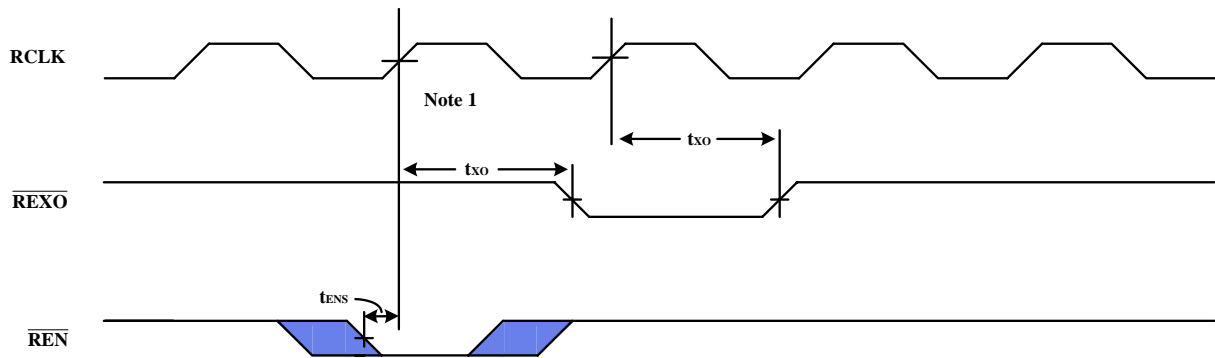
Diagram 11. Half-Full Flag Timing



NOTES:

1. Write to Last Physical Location.

Diagram 12. Write Expansion Out Timing



NOTES:

1. Read from Last Physical Location.

Diagram 13. Read Expansion Out Timing

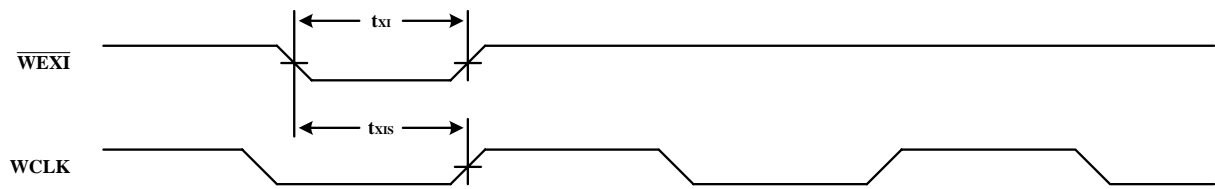


Diagram 14. Write Expansion in Timing

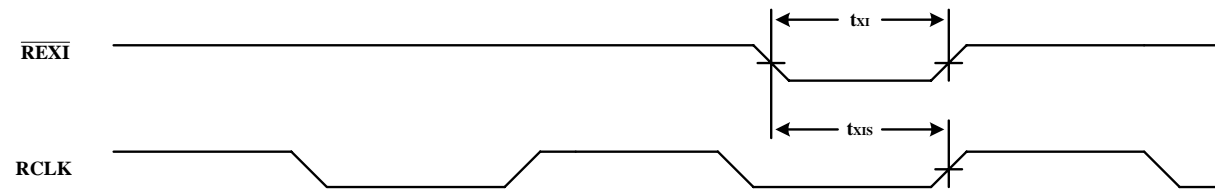
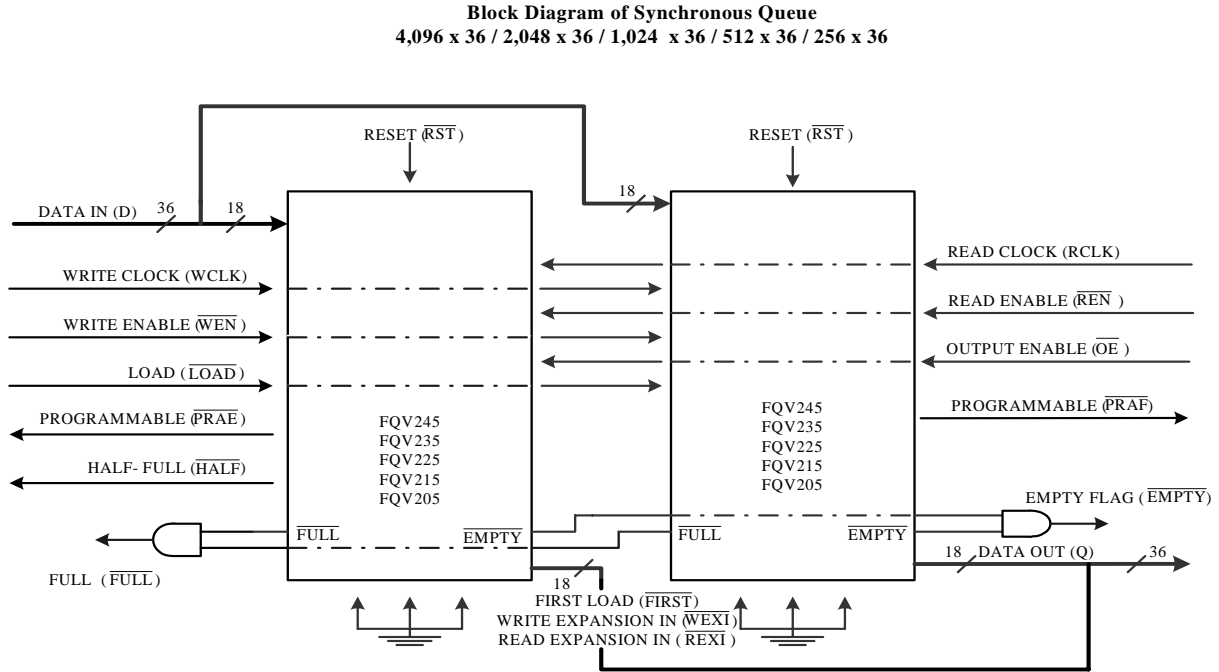


Diagram 15. Read Expansion in Timing

Width Expansion Configuration

Simply connecting together the control signals of multiple devices may increase word width. Status flags can be detected from any one device. The exceptions are the Empty Flag and Full Flag. Because of variations in skew between RCLK and WCLK, it is possible for flag assertion and de-assertion to vary by one cycle between FIFOs. To avoid problems the user must create composite flags by ANDing the Empty Flags of every FIFO, and separately ANDing all Full Flags. Figure 8 demonstrates a 36-bit width by using two FQV245 / 235 / 225 / 215 / 205s. Any word width can be attained by adding additional FQV245 / 235 / 225 / 215 / 205s.



NOTES:

1. Do not connect any output control signals directly together.

Figure 8. Width Expansion Configuration

Depth Expansion Configuration (with Programmable Flags)

These devices can easily be adapted to applications requiring more than 4,096 / 2,048 / 1,024 / 512 / 256 words of buffering. Figure 8 shows Depth Expansion using three FQV245 / 235 / 225 / 215 / 205s. Maximum depth is limited only by signal loading. Follow these steps:

- The first device must be designated by grounding the First Load ($\overline{\text{FIRST}}$) control input.
- All other devices must have $\overline{\text{FIRST}}$ in the high state.
- The Write Expansion Out ($\overline{\text{WEXO}}$) pin of each device must be tied to the Write Expansion In ($\overline{\text{WEXI}}$) pin of the next device.
- The Read Expansion Out ($\overline{\text{REXO}}$) pin of each device must be tied to the Read Expansion In ($\overline{\text{REXI}}$) pin of the next device.
- All Load ($\overline{\text{LOAD}}$) pins are tied together.
- The Half-Full Flag ($\overline{\text{HALF}}$) is not available in this Depth Expansion Configuration.
- $\overline{\text{EMPTY}}$, $\overline{\text{FULL}}$, $\overline{\text{PRAF}}$, and $\overline{\text{PRAE}}$ are created with composite flags by ORing together every respective flags for monitoring. The composite $\overline{\text{PRAF}}$ and $\overline{\text{PRAE}}$ flags are not precise.

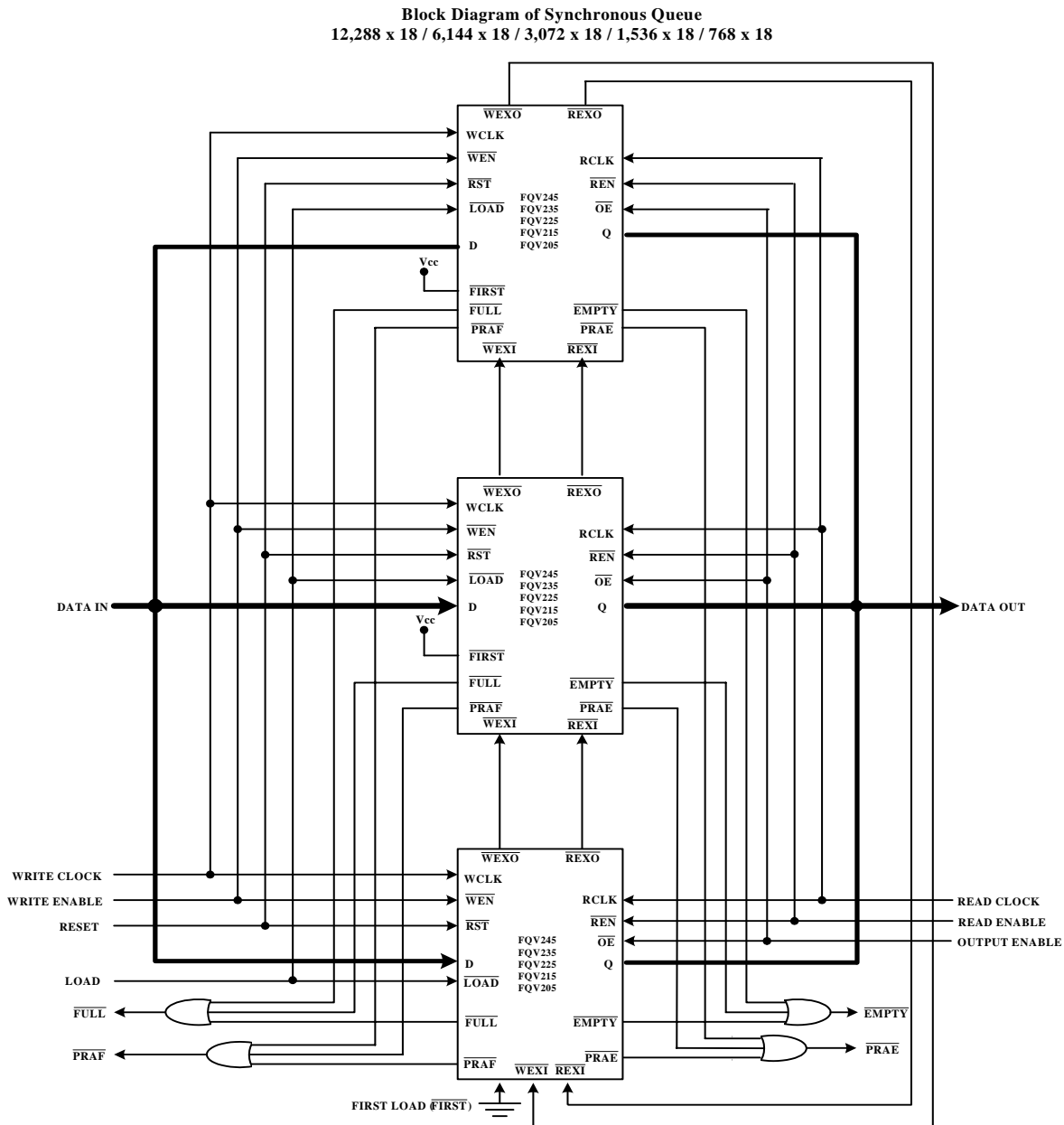


Figure 9. Block Diagram of Multiple Devices with Programmable Flags used in Depth Expansion Configuration



Make Memory Smarter™

Order Information:

HBA Device Family	Device Type	Power†	Speed (ns)*	Package**	Temperature Range	Material
<u>XX</u>	<u>XXXX</u>	<u>X</u>	<u>XX</u>	<u>XX</u>	<u>X</u>	<u>X</u>
FQ	V245 (4,096 x 18)	LB	7-5 – 133 MHz	PF	Blank – Commercial (0°C to 70°C)	Blank – Normal material
	V235 (2,048 x 18)		10 – 100 MHz	TF	I – Industrial (-40° to 85°C)	-F – Pb free material
	V225 (1,024 x 18)		15 – 66 MHz			
	V215 (512 x 18)		20 – 50 MHz			
	V205 (256 x 18)					

†Power – Low (LB)

*Speed – 7.5ns available only in Commercial temp (0°C to 70°C). Slower speeds available upon request.

**Package – 64 pin Plastic Thin Quad Flat Pack (TQFP), 64 pin Slim Thin Quad Flat Pack (STQFP)

Example:

FQV235LB7-5TF (32k x 18, 7.5ns, Commercial temp, Normal material)
 FQV225LB10PFI (16k x 18, 10ns, Industrial temp, Normal material)
 FQV225LB10PFI-F (16k x 18, 10ns, Industrial temp, Pb free material)

Document Revision History:

02/06/03 pg. 5, 7, 8, 9, 10, 12, 14
 10/27/05 pg. 26 Add Pb free package type

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